

FORMING A SEMICONDUCTOR STRUCTURE IN
MANUFACTURING A SEMICONDUCTOR DEVICE USING
ONE OR MORE EPITAXIAL GROWTH PROCESSES

5 ABSTRACT

10 In one embodiment, a semiconductor structure used in manufacturing a
semiconductor device includes a substrate layer. The structure also includes first and
second isolation regions formed by etching an oxide layer provided on the substrate
layer to define an epitaxial growth surface of the substrate layer for epitaxial growth
of a substrate material on the epitaxial growth surface between the first and second
isolation regions. The structure also includes an active region that includes the
epitaxially-grown substrate material between the first and second isolation regions,
the active region formed by epitaxially growing the substrate material on the epitaxial
growth surface of the substrate layer.

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